



**200mW High Speed Switching Diode
Reverse Voltage 100 Volts Forward Current 0.15 Ampere**

Features

- High switching speed
- Surface mount package ideally suited for automatic insertion
- For general purpose switching applications

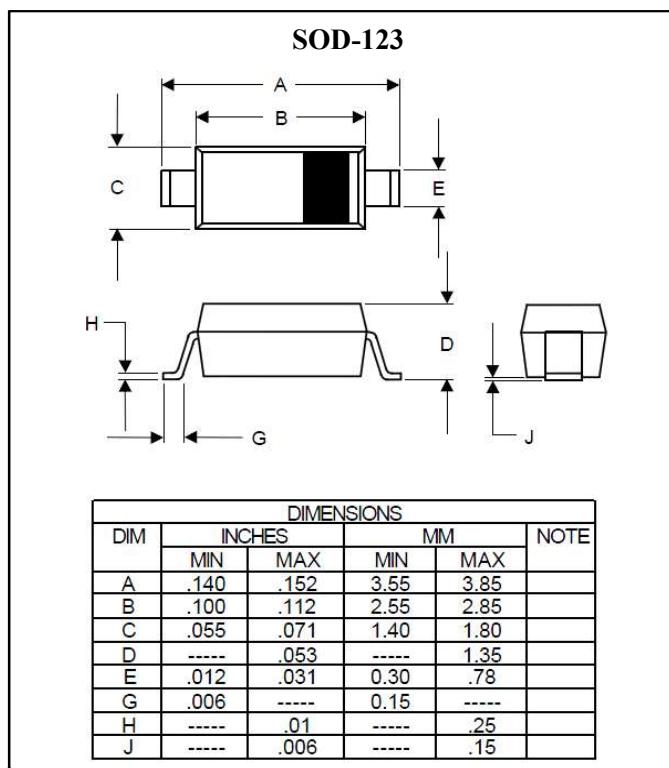
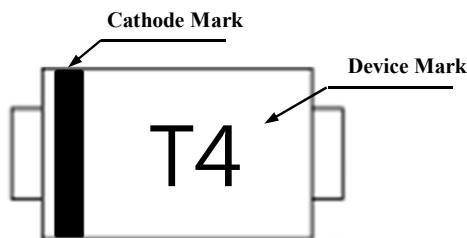
Typical Applications

- High-speed switching.

Mechanical Data

- Case: SOD-123, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Indicated by Cathode Band
- Weight: 0.01 grams (approx.)

Marking



Maximum Ratings & Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rated Value	Unit	Remark
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	100	V	
Reverse Voltage	V _R	75	V	
Average Rectified Current	I _{F(AV)}	150	mA	
Peak Forward Surge Current < 1S	I _{FSM}	350	mA	
Power Dissipation	P _d	200	mW	
Thermal Resistance	R _{th(j-a)}	650	K/W	
Maximum Instantaneous Forward Voltage	V _F	1.0	V	I _F =10mA
Maximum DC Reverse Current at Rated DC Blocking Voltage	I _R	25	nA	V _R =20V, T _j =25 °C
		5.0	uA	V _R =75V, T _j =25 °C
		50.0	uA	V _R =20V, T _j =150 °C
Typical Junction Capacitance	C _J	4.0	pF	Note 1
Maximum Voltage Rise When Switching on (Test with 50mA Pulse)	V _{fr}	2.5	V	Note 2
Maximum Reverse Recovery Time (I _F =10mA, V _R =6V, R _L =100Ω)	trr	4.0	ns	
Maximum Rectification Efficiency (f=100MHz, V _{RF} =2.0V)	n	0.4		
Operation Junction Temperature Range	T _j	-55 to +150	°C	
Storage Temperature Range	T _{STG}	-55 to +150	°C	

Note 1. Measured at 1.0MHz and applied reverse voltage of Zero volts

Note 2. Measured at T_p=0.1us, rise time<30ns and f_p=5 to 100kHz

Ratings and Characteristics Curves (Ta=25°C unless otherwise noted)
